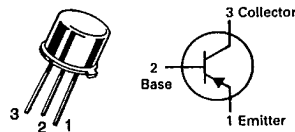


**MAXIMUM RATINGS**

Rating	Symbol	2N4234	2N4235	2N4236	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	60	80	Vdc
Collector-Base Voltage	$V_{CBO}$	40	60	80	Vdc
Emitter-Base Voltage	$V_{EBO}$	7.0			Vdc
Base Current	$I_B$	0.2			Vdc
Collector Current — Continuous	$I_C$	1.0 3.0*			Adc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	1.0 5.7			Watt mW/°C
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	6.0 34			Watts mW/°C
Operating and Storage Junction Temperature Range	$T_J, T_{stg}$	-65 to +200			°C

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	29	°C/W

**2N4234**
**thru**
**2N4236**
**CASE 79-04, STYLE 1  
TO-39 (TO-205AD)**

**GENERAL PURPOSE  
TRANSISTORS**
**PNP SILICON**

T-27-21

# Boca Semiconductor corp.

**3**
**ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)**

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector-Emitter Sustaining Voltage(1) ( $I_C = 100 \text{ mA}$ , $I_B = 0$ )	2N4234 2N4235 2N4236	$V_{CEO(sus)}$	40 60 80	— — —	Vdc
Collector Cutoff Current ( $V_{CE} = 30 \text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 40 \text{ Vdc}$ , $I_B = 0$ ) ( $V_{CE} = 60 \text{ Vdc}$ , $I_B = 0$ )	2N4234 2N4235 2N4236	$I_{CEO}$	— — —	1.0 1.0 1.0	mAdc
Collector Cutoff Current ( $V_{CE} = 40 \text{ Vdc}$ , $V_{BE} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = 60 \text{ Vdc}$ , $V_{BE} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = 80 \text{ Vdc}$ , $V_{BE} = 1.5 \text{ Vdc}$ ) ( $V_{CE} = 30 \text{ Vdc}$ , $V_{BE} = 1.5 \text{ Vdc}$ , $T_C = 150^\circ\text{C}$ ) ( $V_{CE} = 40 \text{ Vdc}$ , $V_{BE} = 1.5 \text{ Vdc}$ , $T_C = 150^\circ\text{C}$ ) ( $V_{CE} = 60 \text{ Vdc}$ , $V_{BE} = 1.5 \text{ Vdc}$ , $T_C = 150^\circ\text{C}$ )	2N4234 2N4235 2N4236 2N4234 2N4235 2N4236	$I_{CEX}$	— — — — — —	0.1 0.1 0.1 1.0 1.0 1.0	mAdc
Collector Cutoff Current ( $V_{CB} = 40 \text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 60 \text{ Vdc}$ , $I_E = 0$ ) ( $V_{CB} = 80 \text{ Vdc}$ , $I_E = 0$ )	2N4234 2N4235 2N4236	$I_{CBO}$	— — —	0.1 0.1 0.1	mAdc
Emitter Cutoff Current ( $V_{BE} = 7 \text{ Vdc}$ , $I_C = 0$ )		$I_{EBO}$	—	0.5	mAdc

**ON CHARACTERISTICS**

DC Current Gain(1) ( $I_C = 100 \text{ mA}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) ( $I_C = 250 \text{ mA}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) ( $I_C = 500 \text{ mA}$ , $V_{CE} = 1.0 \text{ Vdc}$ ) ( $I_C = 1.0 \text{ A}$ , $V_{CE} = 1.0 \text{ Vdc}$ )		$h_{FE}$	40 30 20 10	— 150 — —	—
Collector-Emitter Saturation Voltage(1) ( $I_C = 1.0 \text{ A}$ , $I_B = 125 \text{ mA}$ )		$V_{CE(sat)}$	—	0.6	Vdc
Base-Emitter Saturation Voltage(1) ( $I_C = 1.0 \text{ A}$ , $I_B = 100 \text{ mA}$ )		$V_{BE(sat)}$	—	1.5	Vdc
Base-Emitter On Voltage ( $I_C = 250 \text{ mA}$ , $V_{CE} = 1.0 \text{ Vdc}$ )		$V_{BE}$	—	1.0	Vdc

**SMALL-SIGNAL CHARACTERISTICS**

Current-Gain — Bandwidth Product ( $I_C = 100 \text{ mA}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ MHz}$ )		$f_T$	3.0	—	MHz
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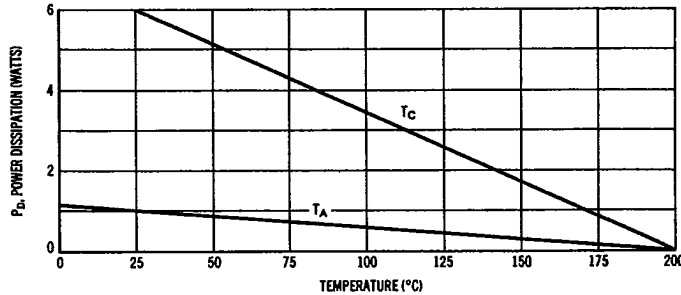
**ELECTRICAL CHARACTERISTICS** (continued) ( $T_A = 25^\circ\text{C}$  unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
Output Capacitance ( $V_{CB} = 10\text{ Vdc}$ , $I_E = 0$ , $f = 100\text{ kHz}$ )	$C_{obo}$	—	100	pF
Small-Signal Current Gain ( $I_C = 50\text{ mAdc}$ , $V_{CE} = 10\text{ Vdc}$ , $f = 1.0\text{ kHz}$ )	$h_{fe}$	25	—	—

(1) Pulse Test:  $PW \leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

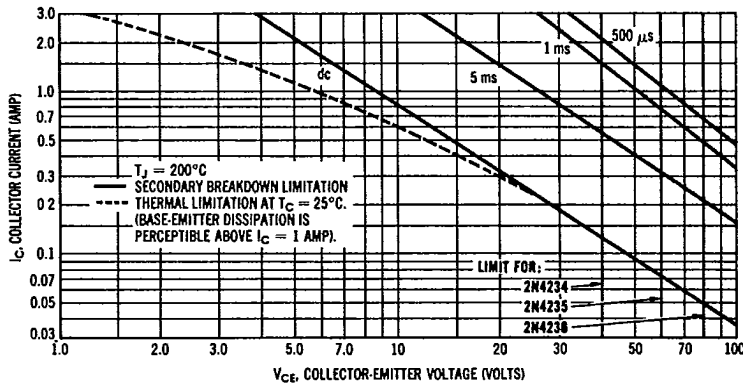
\*Indicates Data in addition to JEDEC Requirements.

**FIGURE 1 — POWER-TEMPERATURE DERATING CURVE**



Safe Area Curves are indicated by Figure 2.  
All limits are applicable and must be observed.

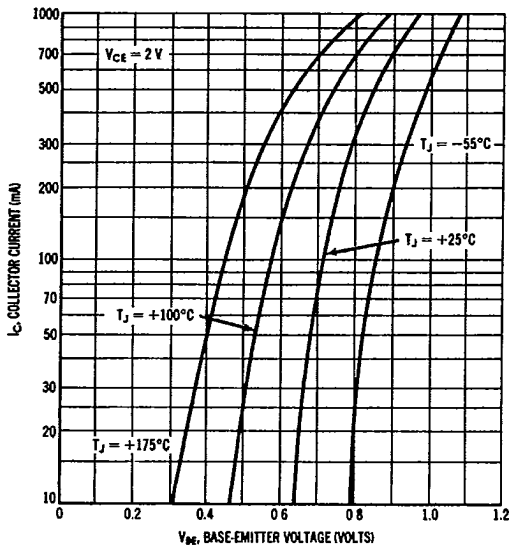
**FIGURE 2 — ACTIVE-REGION SAFE OPERATING AREAS**



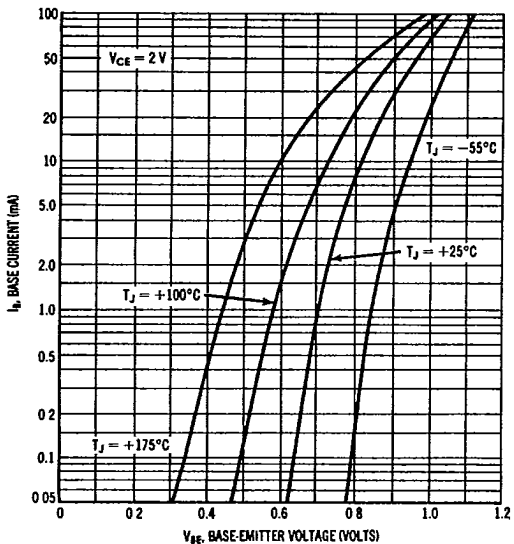
The Safe Operating Area Curves indicate  $I_C - V_{CE}$  limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum  $T_J$ , power-temperature derating must be observed for both steady state and pulse power conditions.

**LARGE SIGNAL CHARACTERISTICS**

**FIGURE 3 — TRANSCONDUCTANCE**

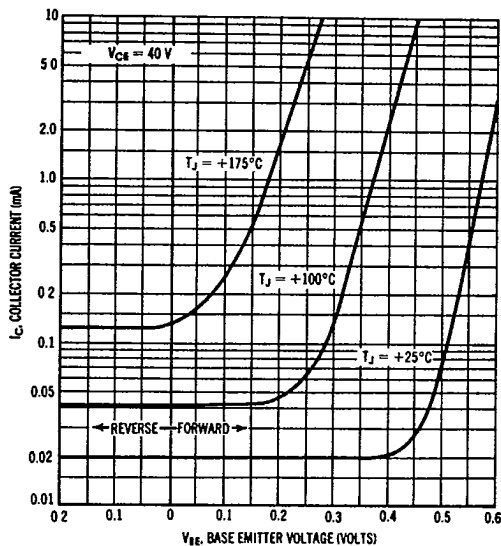


**FIGURE 4 — INPUT ADMITTANCE**

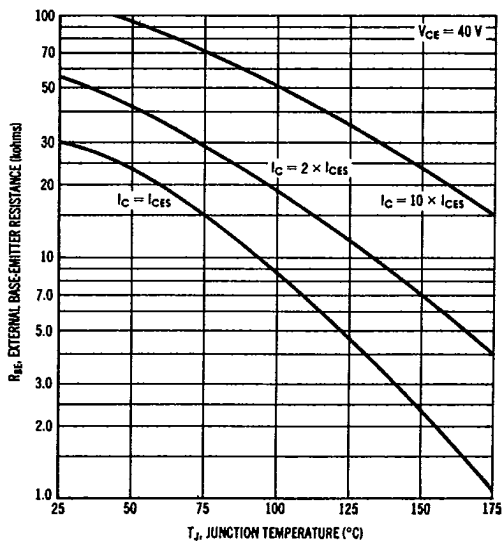


**"OFF" REGION CHARACTERISTICS**

**FIGURE 5 — TRANSCONDUCTANCE**

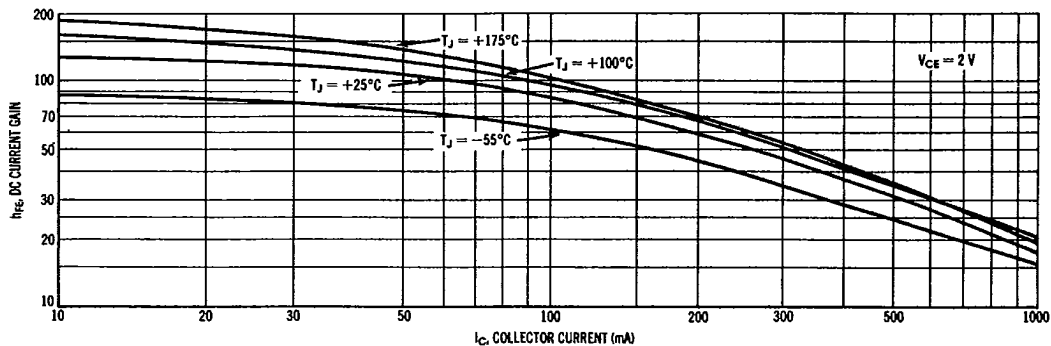


**FIGURE 6 — EFFECTS OF BASE-EMITTER RESISTANCE**



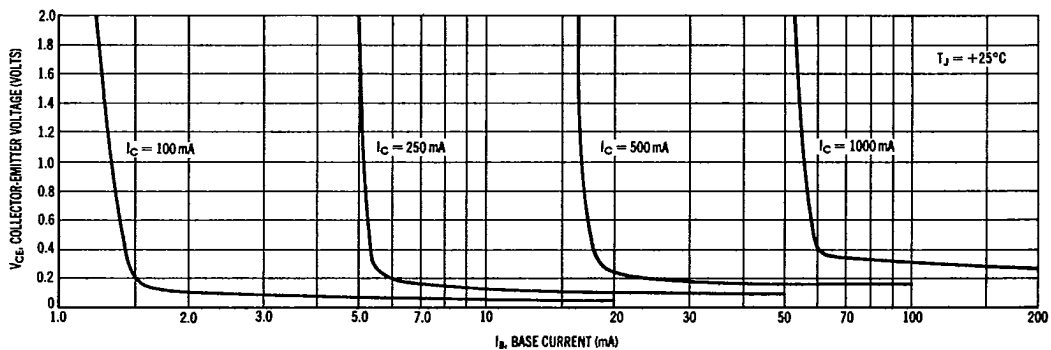
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FIGURE 7 — CURRENT GAIN



SATURATION REGION CHARACTERISTICS

FIGURE 8 — COLLECTOR SATURATION REGION



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FIGURE 9 — "ON" VOLTAGES

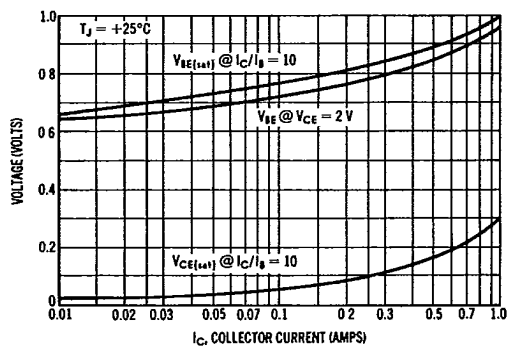


FIGURE 10 — TEMPERATURE COEFFICIENTS

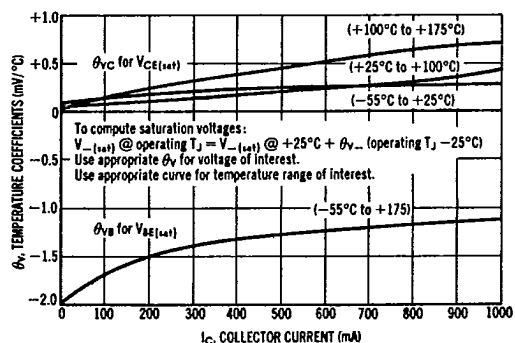


FIGURE 11 — TURN-ON TIME

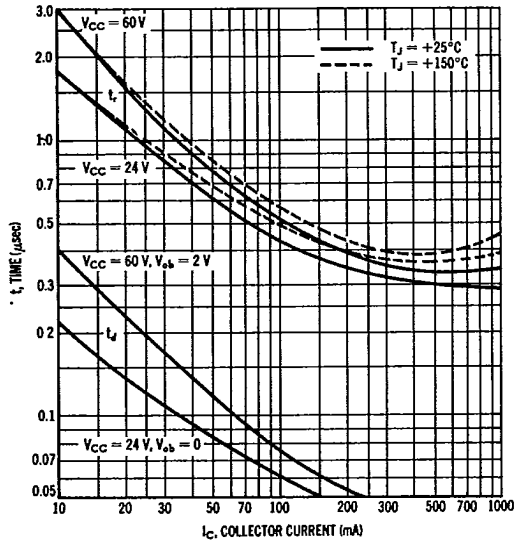
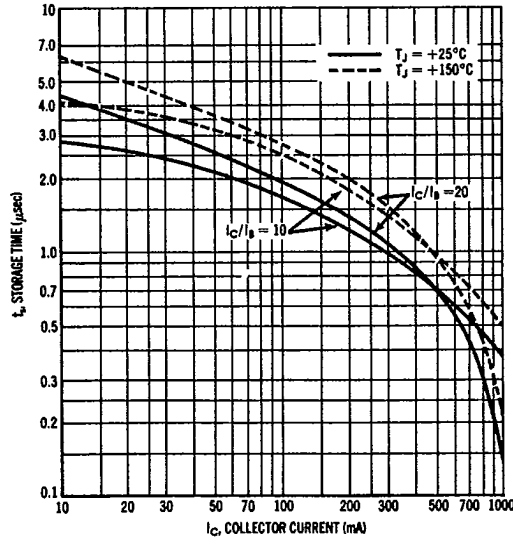


FIGURE 12 — STORAGE TIME



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FIGURE 13 — CAPACITANCE

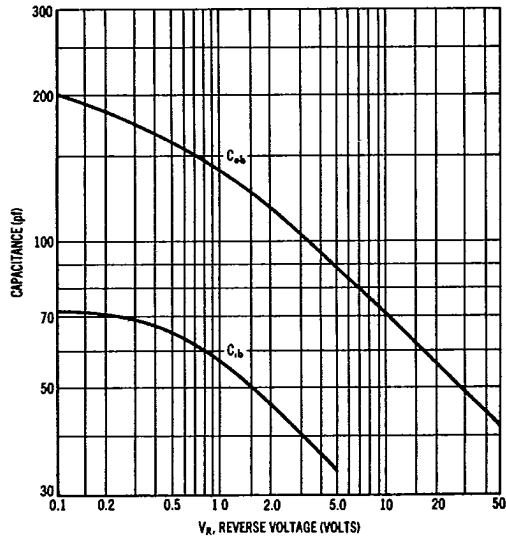


FIGURE 14 — FALL TIME

